

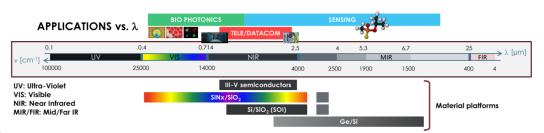


Benefits of Silicon Nitride



Large transparency window: 400 – 4'000 nm

Reference Silicon: 1'100 – 4'000 nm



Muñoz et. al., Sensors **2017**, 17, 2088

Low propagation loss: < 1dB/m possible Reference Silicon: 2.5 to 1 dB/cm

High optical power: > 5 W per waveguide (10⁹W/cm²)
Reference Silicon: 0.1 W per waveguide

Scalable to volume



required for may applications

Photonic Integration: Motivation for low loss PICs

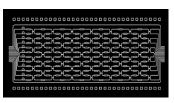
Why are losses important?



- Long delay lines require of 10s of cm
- Detection of photons coming back
- Phase noise is related to losses

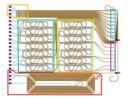


- Phase noise of AWGs is related to losses
- Tunable narrow linewidth lasers
- Narrow linewidth Filter

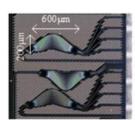


- Assymetric MZI interferometers
- High Q ring resonators
- Every photon counts

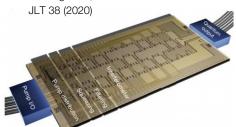




Martin et al., JLT 36 (2018)



Cheung et al.,



Arrazola et al., Nature 54 March 2021

Versatile Platform



3+ thicknesses

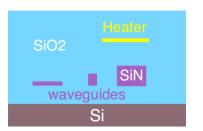
10+ process modules

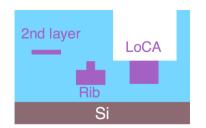
800 nm

350 nm

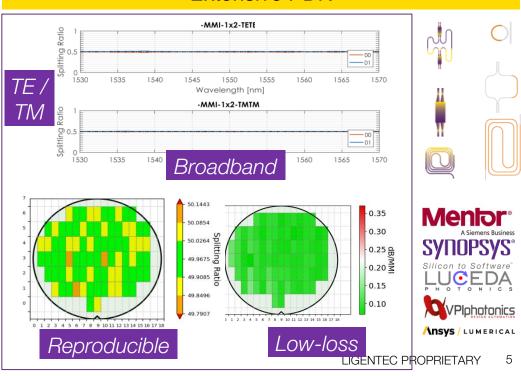
150 nm

custom





Extensive PDK



Simplify the access to PIC technology

Seamless journey from Idea to Volumes



Entry: R&D & Prototyping Open access, low barrier

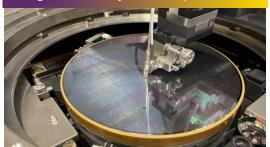


Fast prototyping

- Established technology
- Fixed layer stack
- Extensive PDK
- Regular MPW runs
- Custom runs
- Design / layout support
- Characterization
- Packaging support

Optimize: Development

High flexibility & competence



Custom PIC Developments

- Engineering studies
- Layer stack adaptation
- Custom integrations

Ligentec Labs

Early technology access

Manufacturing: Supply Quality and guarantee



Pilot Fabrication

Pilot and niche quantities

Volume Fabrication

- Large volumes
- High-capacity wafer fab
- Fully automated testing
- Automotive quality system

The next step – enhance the SiN PIC platform



SiN – The platform for monolithic & heterogeneous integration

Use SiN as base platform for general circuitry

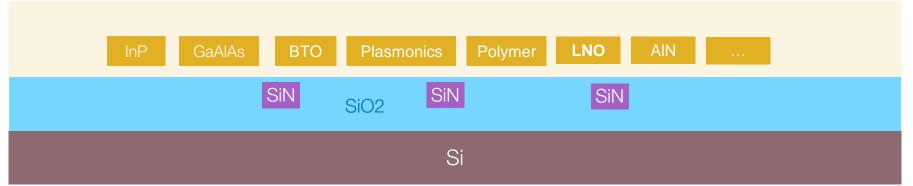
- Comprehensive PDK
- Standard I/Os
- Scalable to volume

Add materials as required by application



100 GHz bandwidth, 1 volt integrated electro-optic Mach-Zehnder modulator at near-IR wavelengths

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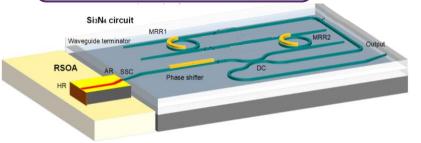


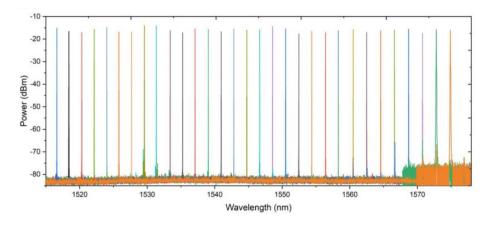
Hybrid Integration example

Tunable Narrow Linewidth Lasers









RSOA Phase shifter MRR2

Narrow Linewidth External Cavity Lasers

Linewidth: <3kHz

SMSR: -70dB

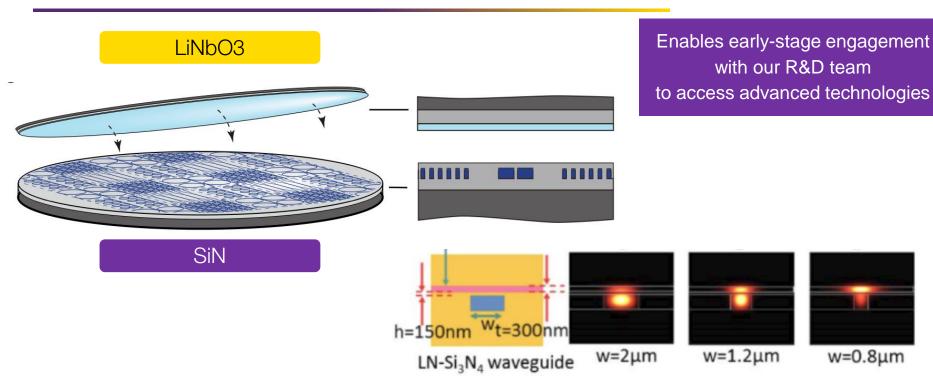
Max power: 34mW

Tuning: 58.5nm

Heterogenous Integration example

LNOI / SiN wafer level bonding

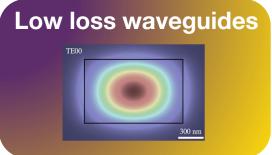




Summary

Low Loss SiN - Platform Overview





MPW / Dedicated runs Short turn around

Flexible R&D line Volume line





Actives Integration





